

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (drain with (I/O or pad or input/output or input near output)) and (source with ring) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:37
L2	0	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:35
L3	0	(257/355 or 257/356 or 257/360 or 257/365 or 257/546 or 257/401 or 257/371).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (drain with (I/O or pad or input/output or input near output)) and (source with ring) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:36
L4	0	(257/355 or 257/356 or 257/360 or 257/365 or 257/546 or 257/401 or 257/371).ccls. and (drain with (I/O or pad or input/output or input near output)) and (source with ring) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:37
L5	0	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:38
L6	26	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (gate with (vdd near10 (I/O or pad or input/output or (input near output))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:47

L7	4	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (gate with (vdd near10 (I/O or pad or input/output or (input near output)))) and (drain with (I/O or pad or input/output or input near output)) and (source with ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:41
L8	34	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (gate with (vdd near10 (I/O or pad or input/output or (input near output))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:47
S1	2553	(257/355 or 257/356 or 257/361 or 257/365).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:13
S2	2887	(257/355 or 257/356 or 257/360 or 257/365).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:13
S3	3138	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 21:00
S4	488	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 near4 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:26
S5	490	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 near4 gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:29
S6	772	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:32
S7	42019	(semiconductor or esd or discharge or protection) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:54
S8	28889	(semiconductor or esd or discharge or protection) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (well or tub or tank)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:55

S9	14062	(semiconductor or esd or discharge or protection) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (well or tub or tank) and (ring or isolat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:55
S10	5248	(semiconductor) and (esd or discharge or protection) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (well or tub or tank) and (ring or isolat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:56
S11	897	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (well or tub or tank) and (ring or isolat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:57
S12	580	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and ((well or tub or tank) same (ring or isolat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 20:57
S13	536	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and ((well or tub or tank) same (ring or isolat\$3)) and (resistor or resistance or resistive)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:06
S14	5044	(257/355 or 257/356 or 257/360 or 257/365 or 257/546 or 257/401 or 257/371).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:37
S15	1000	(257/355 or 257/356 or 257/360 or 257/365 or 257/546 or 257/401 or 257/371).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 09:36
S16	261	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and ((well or tub or tank) same (ring or isolat\$3)) and (resistor or resistance or resistive) and ((ring or isolat\$3) with (vdd or vss or voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 07:02

S17	25	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (twin adj wells) and (resistor or resistance or resistive)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 07:02
S18	25	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (twin adj wells)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/19 21:54
S19	1	(semiconductor or ESD) and (guard adj ring or well adj ring) and well and (gate with (resistor near10 vss)) and (ring with vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 03:41
S20	17	(semiconductor or ESD) and (guard adj ring or well adj ring) and well and (gate with (resistor near10 vss))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 03:55
S21	44	(semiconductor or ESD) and (guard adj ring or well adj ring) and well and (ring with (vdd))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 03:55
S22	16	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (ring with (PMOSFET or PMOS or PFET or (p near3 (MOS or FET or MOSFET))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:30
S23	16	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and Salling.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:24
S24	97	Salling.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:24
S25	44	(semiconductor) and (esd or electro?static) and (ring with (PMOSFET or PMOS or PFET or (p near3 (MOS or FET or MOSFET))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:47
S26	8	(semiconductor) and (esd or electro?static) and ((ring with (PMOSFET or PMOS or PFET or (p near3 (MOS or FET or MOSFET)))) same (trigger or node))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:31

S27	2	("20040100745").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/20 06:49
S28	2	"20040100745".pn. and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/20 06:49